

## A2.2 (M. Hetterich)

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$x\text{Mn}_x\text{Se}$ , 4<sup>th</sup> Int. Conf. on Spectroscopic Ellipsometry (ICSE 4), Stockholm, Sweden, 2007, phys. status solidi (c) **5**, 1007 (2008)

[A2.2:46] ‡ K.C. Agarwal, B. Daniel, C. Klingshirn, M. Hetterich, H. Saito, S. Yuasa, and K. Ando, *Magneto-optical studies on magnetic semiconductors*, invited, Int. Conf. on Magnetic Materials (ICMM-2007), Kolkata, India, 2007, AIP Conf. Proc. **1003**, 225 (2008)

### Invited Talks

M. Hetterich, *(Zn,Mn)Se – Material properties and application in (In,Ga)As-based spin injection devices*, invited seminar talk (Seminar des Sonderforschungsbereichs 410: II–VI-Halbleiter: Wachstumsmechanismen, niederdimensionale Strukturen und Grenzflächen), Würzburg (Germany), December 01, 2005

M. Hetterich, W. Löffler, J. Fallert, N. Höpcke, H. Burger, T. Passow, S. Li, B. Daniel, B. Ramadout, J. Lupaca-Schomber, J. Hetterich, D. Litvinov, D. Gerthsen, C. Klingshirn, and H. Kalt, *Electrical spin injection into InGa(N)As quantum structures and single InGaAs quantum dots*, invited keynote lecture, 7<sup>th</sup> Int. Conf. on Excitonic Processes in Condensed Matter (EXCON 2006), Winston-Salem, NC (USA), June 28, 2006. Corresponding invited paper published in phys. status solidi (b) **243**, 3812 (2006)

D. Litvinov, D. Gerthsen, A. Rosenauer, M. Schowalter, T. Passow, and M. Hetterich, *The role of segregation in InGaAs heteroepitaxy*, THERMEC' 2006, Vancouver (Canada), July 2006

M. Hetterich, F.M. Weber, M. Karl, J. Lupaca-Schomber, W. Löffler, S. Li, T. Passow, J. Hawecker, D. Gerthsen, and H. Kalt, *Pyramidal and pillar-type optical cavities*, Symposium Nano Optics, Konrad-Zuse-Zentrum für Informationstechnik (ZIB), Berlin (Germany), October 19, 2006

W. Löffler, M. Hetterich, and H. Kalt, *Quanteninformationsverarbeitung mit Halbleiterquantenpunkten und Cavities*, Symposium Nano Optics, Konrad-Zuse-Zentrum für Informationstechnik (ZIB), Berlin (Germany), October 19, 2006

M. Hetterich, W. Löffler, N. Höpcke, C. Mauser, J. Fallert, T. Passow, S. Li, B. Daniel, B. Ramadout, J. Lupaca-Schomber, J. Hetterich, D. Litvinov, D. Gerthsen, and H. Kalt, *Electrical spin injection into InGaAs quantum dot ensembles and single quantum dots*, SFB 491 Int. Workshop on Quantum-Dot Spintronics, Bochum (Germany), December 08, 2006

M. Hetterich, W. Löffler, N. Höpcke, C. Mauser, J. Fallert, H. Burger, T. Passow, S. Li, B. Daniel, B. Ramadout, J. Lupaca-Schomber, J. Hetterich, C. Klingshirn, D. Litvinov, D. Gerthsen, and H. Kalt, *Optical cavities and electrical spin injection into single quantum dots – Concepts for a possible spin-based quantum information processing*, "Frontier Developments in Optics and Spectroscopy", Int. School of Atomic and Molecular Spectroscopy, Ettore Majorana Center for Scientific Culture, Erice, Sicily (Italy), June 17 – July 02, 2007 (corresponding invited book chapter to be published in summer school proceedings)

M. Hetterich, *Neuartige GaIn(N)As-basierte Halbleiter-Bauelemente für die Optoelektronik und spinbasierte Quanteninformationsverarbeitung*, laureate talk Carl Freudenberg award, Karlsruhe (Germany), January 25, 2008

M. Hetterich, W. Löffler, P. Aßhoff, T. Passow, D. Litvinov, D. Gerthsen, and H. Kalt, *Electrical spin injection into single InGaAs quantum dots*, Spring Meeting of the Deutsche Physikalische Gesellschaft (DPG), Berlin (Germany), February 26, 2008. Corresponding invited book chapter to be published in: *Advances in solid state physics*, Vol. 48, R. Haug (Ed.), Springer, Berlin, Heidelberg, New York

